



SEMIPACK® 2

## Thyristor Modules

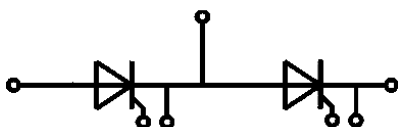
## SKKT 215/16 E

## Features

- Heat transfer through aluminium oxide ceramic insulated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E63532

## Typical Applications\*

- DC motor control (e. g. for machine tools)
- AC motor soft starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)



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## Absolute Maximum Ratings

| Symbol         | Conditions            |                       | Values      | Unit             |
|----------------|-----------------------|-----------------------|-------------|------------------|
| <b>Chip</b>    |                       |                       |             |                  |
| $I_{T(AV)}$    | sinus 180°            | $T_c = 85\text{ °C}$  | 215         | A                |
|                |                       | $T_c = 100\text{ °C}$ | 153         | A                |
| $I_{TSM}$      | 10 ms                 | $T_j = 25\text{ °C}$  | 7000        | A                |
|                |                       | $T_j = 125\text{ °C}$ | 5700        | A                |
| $i^2t$         |                       | $T_j = 25\text{ °C}$  | 245000      | A <sup>2</sup> s |
|                | 10 ms                 | $T_j = 125\text{ °C}$ | 162450      | A <sup>2</sup> s |
| $V_{RSM}$      |                       |                       | 1700        | V                |
| $V_{RRM}$      |                       |                       | 1600        | V                |
| $V_{DRM}$      |                       |                       | 1600        | V                |
| $(di/dt)_{cr}$ | $T_j = 125\text{ °C}$ |                       | 200         | A/μs             |
| $(dv/dt)_{cr}$ | $T_j = 125\text{ °C}$ |                       | 1000        | V/μs             |
| $T_j$          |                       |                       | -40 ... 125 | °C               |
| <b>Module</b>  |                       |                       |             |                  |
| $T_{stg}$      |                       |                       | -40 ... 125 | °C               |
| $V_{isol}$     | a.c.; 50 Hz; r.m.s.   | 1 min                 | 3000        | V                |
|                |                       | 1 s                   | 3600        | V                |

## Characteristics

| Symbol                            | Conditions                                                                                       |            | min. | typ.  | max.     | Unit             |
|-----------------------------------|--------------------------------------------------------------------------------------------------|------------|------|-------|----------|------------------|
| Chip                              |                                                                                                  |            |      |       |          |                  |
| V <sub>T</sub>                    | T <sub>j</sub> = 25 °C, I <sub>T</sub> = 600 A                                                   |            |      |       | 1.5      | V                |
| V <sub>T(TO)</sub>                | T <sub>j</sub> = 125 °C                                                                          |            |      |       | 0.85     | V                |
| r <sub>T</sub>                    | T <sub>j</sub> = 125 °C                                                                          |            |      |       | 1.2      | mΩ               |
| I <sub>DD</sub> ; I <sub>RD</sub> | T <sub>j</sub> = 125 °C, V <sub>DD</sub> = V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> |            |      |       | 60       | mA               |
| t <sub>gd</sub>                   | T <sub>j</sub> = 25 °C, I <sub>G</sub> = 1 A, di <sub>G</sub> /dt = 1 A/μs                       |            |      | 1     |          | μs               |
| t <sub>gr</sub>                   | V <sub>D</sub> = 0.67 * V <sub>DRM</sub>                                                         |            |      | 2     |          | μs               |
| t <sub>q</sub>                    | T <sub>j</sub> = 125 °C                                                                          |            |      | 150   |          | μs               |
| I <sub>H</sub>                    | T <sub>j</sub> = 25 °C                                                                           |            |      | 150   | 400      | mA               |
| I <sub>L</sub>                    | T <sub>j</sub> = 25 °C, R <sub>G</sub> = 33 Ω                                                    |            |      | 300   | 1000     | mA               |
| V <sub>GT</sub>                   | T <sub>j</sub> = 25 °C, d.c.                                                                     |            | 2    |       |          | V                |
| I <sub>GT</sub>                   | T <sub>j</sub> = 25 °C, d.c.                                                                     |            | 150  |       |          | mA               |
| V <sub>GD</sub>                   | T <sub>j</sub> = 125 °C, d.c.                                                                    |            |      |       | 0.25     | V                |
| I <sub>GD</sub>                   | T <sub>j</sub> = 125 °C, d.c.                                                                    |            |      |       | 10       | mA               |
| R <sub>th(j-c)</sub>              | cont.                                                                                            | per chip   |      |       | 0.12     | K/W              |
|                                   |                                                                                                  | per module |      |       | 0.06     | K/W              |
| R <sub>th(j-c)</sub>              | sin. 180°                                                                                        | per chip   |      |       | 0.125    | K/W              |
|                                   |                                                                                                  | per module |      |       | 0.065    | K/W              |
| R <sub>th(j-c)</sub>              | rec. 120°                                                                                        | per chip   |      |       | 0.14     | K/W              |
|                                   |                                                                                                  | per module |      |       | 0.07     | K/W              |
| Module                            |                                                                                                  |            |      |       |          |                  |
| R <sub>th(c-s)</sub>              | chip                                                                                             |            |      | 0.04  |          | K/W              |
|                                   | module                                                                                           |            |      | 0.027 |          | K/W              |
| M <sub>s</sub>                    | to heatsink M5                                                                                   |            | 4.25 |       | 5.75     | Nm               |
| M <sub>t</sub>                    | to terminals M6                                                                                  |            | 4.25 |       | 5.75     | Nm               |
| a                                 |                                                                                                  |            |      |       | 5 * 9.81 | m/s <sup>2</sup> |
| w                                 |                                                                                                  |            |      | 165   |          | g                |

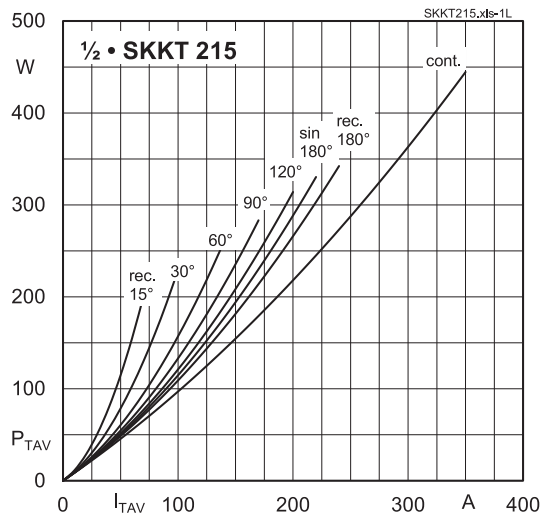


Fig. 1L: Power dissipation per thyristor vs. on-state current

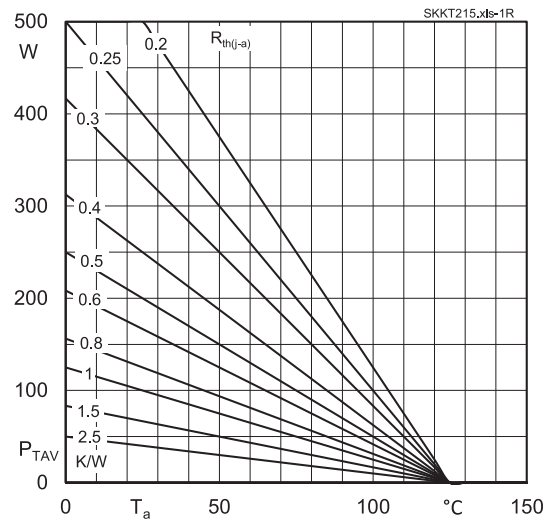


Fig. 1R: Max. power dissipation per chip vs. ambient temperature

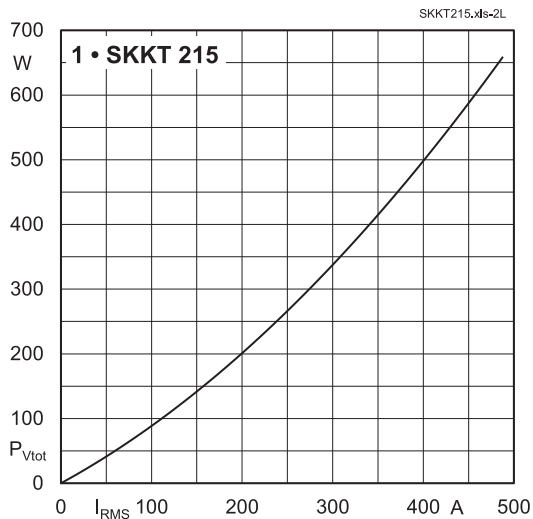


Fig. 2L: Max. power dissipation of one module vs. rms current

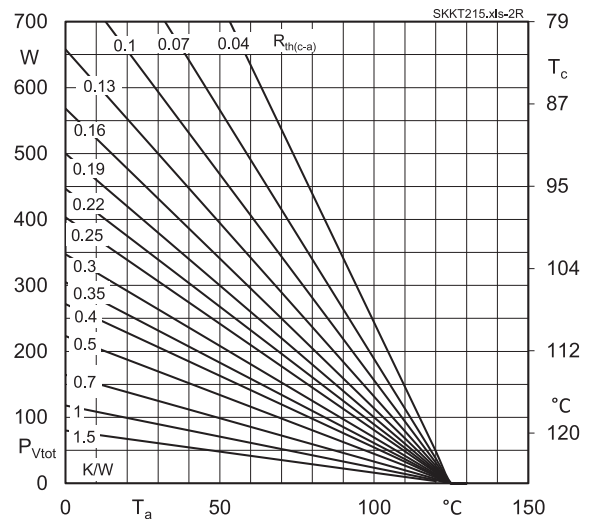


Fig. 2R: Max. power dissipation of one module vs. case temperature

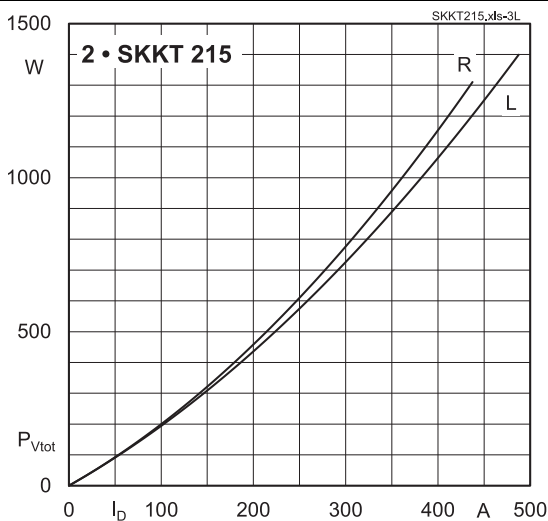


Fig. 3L: Max. power dissipation of two modules vs. direct current

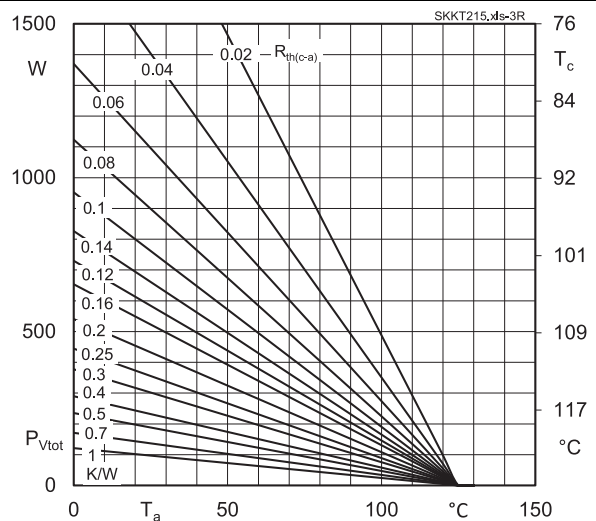


Fig. 3R: Max. power dissipation of two modules vs. case temperature

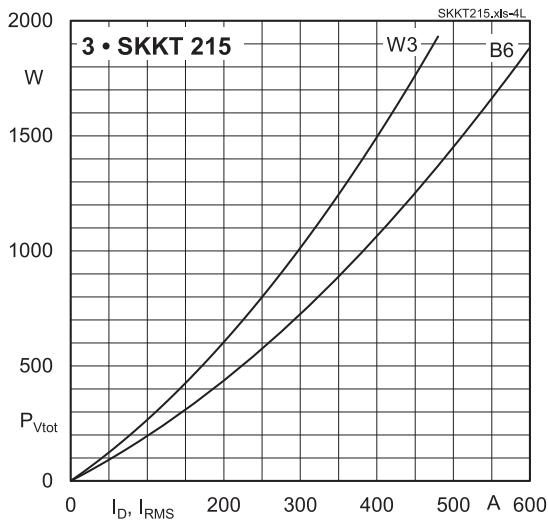


Fig. 4L: Max. power dissipation of three modules vs. direct current

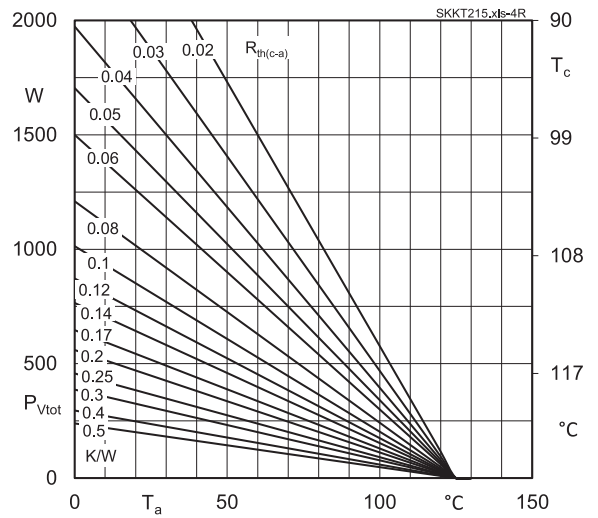


Fig. 4R: Max. power dissipation of three modules vs. case temperature

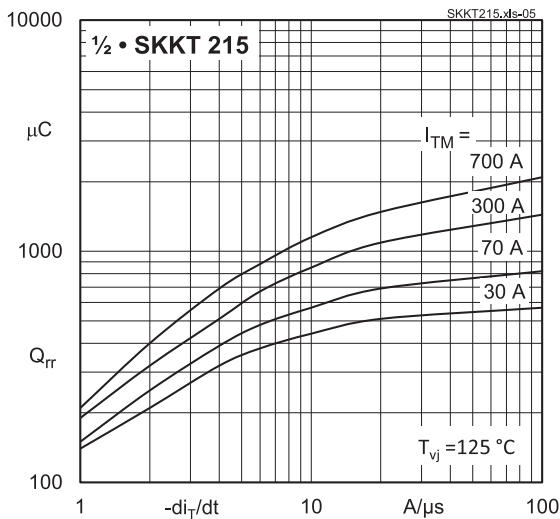


Fig. 5: Recovered charge vs. current decrease

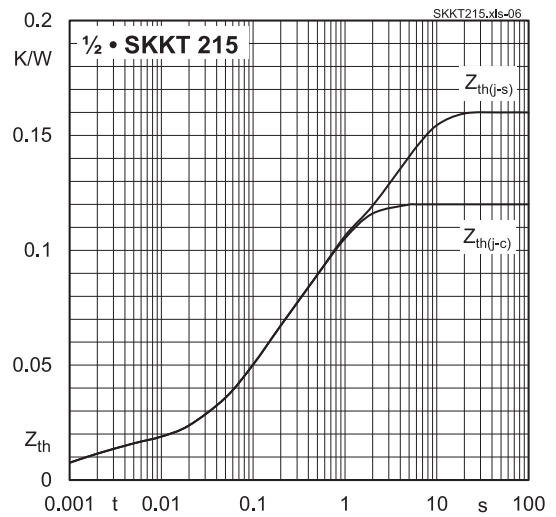


Fig. 6: Transient thermal impedance vs. time

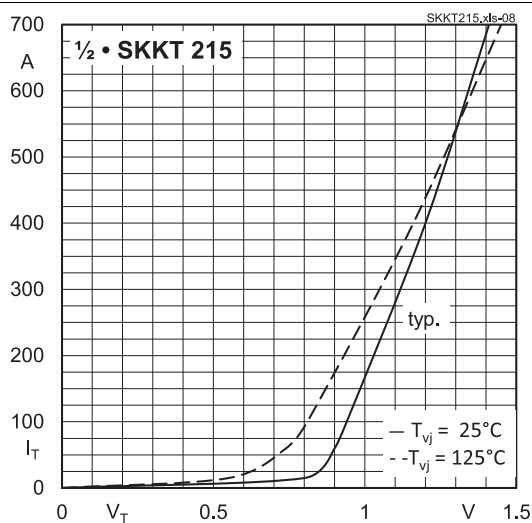


Fig. 7: On-state characteristics

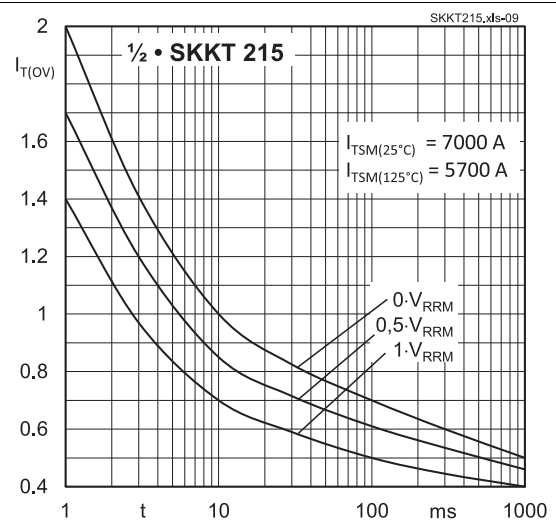


Fig. 8: Surge overload current vs. time

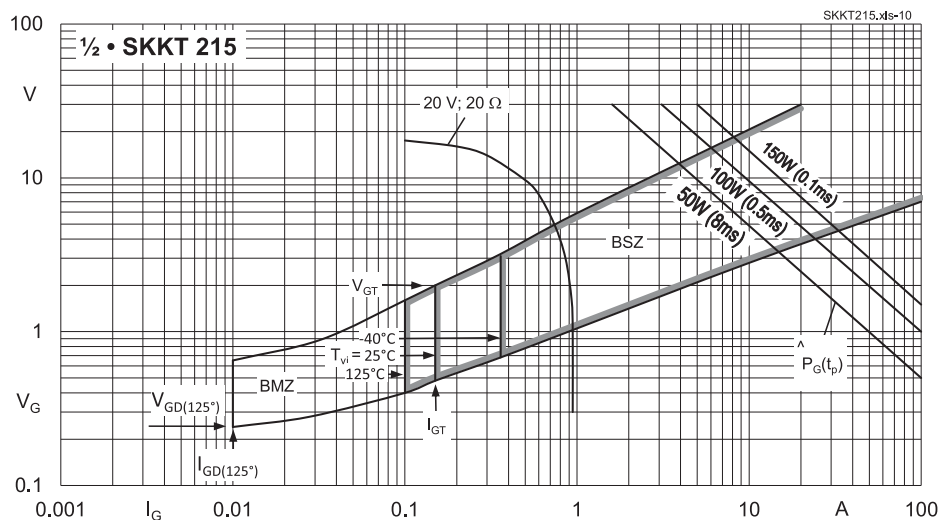
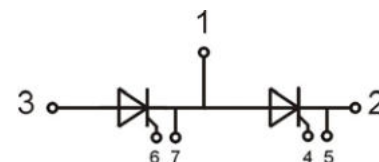
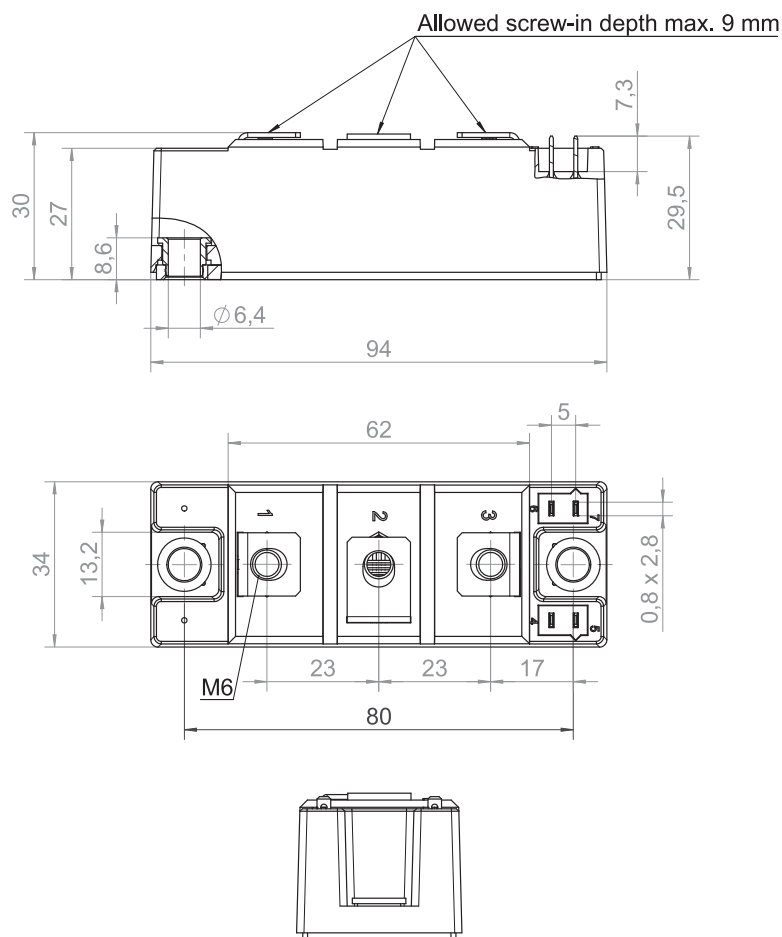


Fig. 9: Gate trigger characteristics



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

## \*IMPORTANT INFORMATION AND WARNINGS

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